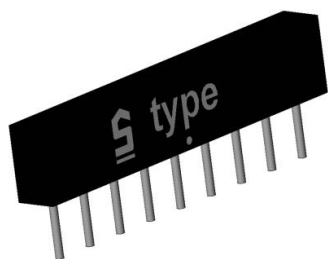


DAN 801, DAP 801 (200mW) ...



Diode arrays

Silicon rectifiers arrays

DAN 801, DAP 801 (200mW)

Forward Current: 0,1 A

Reverse Voltage: 80 to / V

Publish Data

Features

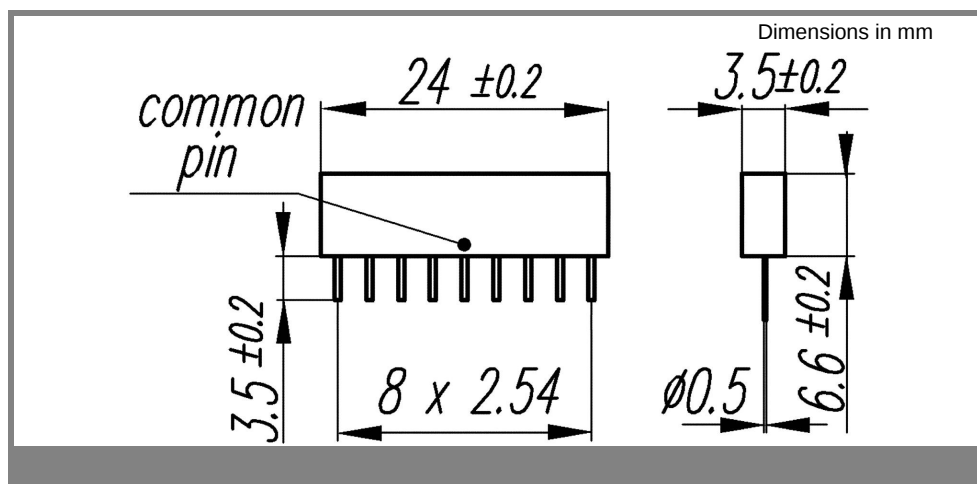
Mechanical Data

- 9 Pin - plastic case
- Terminals: plated terminals solderable per IEC 68-2-20
- Mounting position : any
- Weigh approx. 0,6 g
- Standard packing : bulk
- DAP 801 - common anodes
- DAN 801- common cathodes
- ¹⁾ Valid for one branch; per diode for simultaneous operation $I_{FAV} = 25 \text{ mA}$
- ²⁾ $I_F = 10 \text{ mA}$, $T_A = 25^\circ\text{C}$

Type	Repetitive peak reverse voltage	Surge peak reverse voltage	Max. reverse recovery time	Max. forward voltage
	V_{RRM} V	V_{RSM} V	$I_F = 10 \text{ mA}$ $I_R = 10 \text{ mA}$ $I_{RR} = 1 \text{ mA}$ t_{rr} ns	$V_F^{2)}$
DAN 803	80	80	4	1,0
DAP 803	80	80	4	1,0

Absolute Maximum Ratings		$T_C = 25^\circ\text{C}$ unless otherwise specified	
Symbol	Conditions	Values	Units
I_{FAV}	Max. averaged fwd. current, R-load, $T_A = 25^\circ\text{C}$ ¹⁾	0,1	A
I_{FRM}	Repetitive peak forward current $f > 15 \text{ Hz}$ ¹⁾	0,2	A
I_{FSM}	Peak forward surge current 50 Hz half sinus-wave ³⁾	0,5	A
i^2t	Rating for fusing, $t < 10 \text{ ms}$ ³⁾	0,0012	A^2s
R_{thA}	Max. thermal resistance junction to ambient ¹⁾	85	K/W
R_{thT}	Max. thermal resistance junction to terminals ¹⁾	/	K/W
T_j	Operating junction temperature	-50 ... +150	$^\circ\text{C}$
T_s	Storage temperature	-50 ... +150	$^\circ\text{C}$

Characteristics		$T_C = 25^\circ\text{C}$ unless otherwise specified	
Symbol	Conditions	Values	Units
I_R	Maximum leakage current, $T_j = 25^\circ\text{C}$; $V_R = V_{RRM}$	< 25 (note : $V_R = 20 \text{ V}$)	nA
	$T_j = ^\circ\text{C}$; $V_R = V_{RRM}$		
C_J	Typical junction capacitance (at MHz and applied reverse voltage of V)	/	pF
Q_{rr}	Reverse recovery charge ($U_R = V$; $I_F = A$; $dI_F/dt = A/\text{ms}$)	/	μC
E_{RSM}	Non repetitive peak reverse avalanche energy ($I_R = \text{mA}$; $T_j = ^\circ\text{C}$; inductive load switched off)		mJ



DAN 801, DAP 801 (200mW) ...

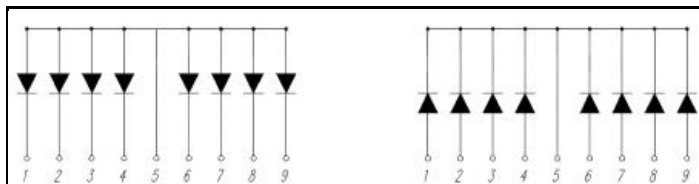


Fig. 1 : DAP 801 (Com.anodes) DAP 803 (Com. cathodes)